ABSTRACT

The present invention is a process for plasma enhanced fabrication of conductive materials on a substrate comprising the steps of placing substrate in an inductively coupled (IC) plasma reaction chamber and maintaining the chamber under vacuum pressure while introducing at least a preselected reactant species gas, and optionally a carrier gas into the chamber for a preselected fabrication procedure on the substrate. A plasma is generated from the gas or gases within the chamber using a power source inductively coupled to the reaction chamber. After the consequent fabrication procedure the substrate is removed from the > add A5